

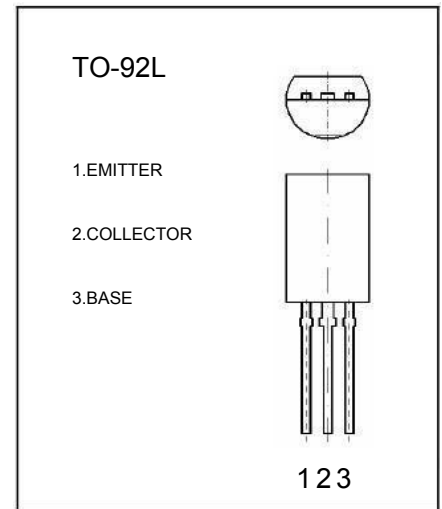


# TO-92L Plastic-Encapsulate Transistors

## A935 TRANSISTOR(PNP)

### FEATURES

Low collector to emitter saturation voltage  $V_{CE(sat)}$ .



### MAXIMUM RATINGS ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Units
$V_{CB0}$	Collector-Base Voltage	- 80	V
$V_{CE0}$	Collector-Emitter Voltage	- 80	V
$V_{EB0}$	Emitter-Base Voltage	-5	V
$I_c$	Collector Current –Continuous	-0.7	A
$P_c$	Collector Power Dissipation	0.75	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55-150	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_c=-50\mu\text{A}, I_E=0$	-80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_c=-2\text{mA}, I_B=0$	-80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-50\mu\text{A}, I_c=0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-50\text{V}, I_E=0$			-0.5	$\mu\text{A}$
<b>Emitter cut-off current</b>	$I_{EBO}$	$V_{EB}=-4\text{V}, I_c=0$			-0.5	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE}=-3\text{V}, I_c=-100\text{mA}$	82		390	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c=-500\text{mA}, I_B=-50\text{mA}$			-0.4	V
Transition frequency	$f_T$	$V_{CE}=-10\text{V}, I_E=-50\text{mA}$		100		MHz

### CLASSIFICATION OF $h_{FE(1)}$

Rank	P	Q	R
Range	82-180	120-270	180-390

